ABSOLUTE MAXIMUM RATINGS

V _{DD} to AGND0.3V to +7V
AGND to DGND0.3V to +0.3V
REF to AGND0.3V to (V _{DD} + 0.3V)
REFADJ to AGND0.3V to (V _{DD} + 0.3V)
Digital Inputs to DGND0.3V to (V _{DD} + 0.3V)
Digital Outputs to DGND0.3V to (V _{DD} + 0.3V)
CH0-CH7 to AGND±16.5V
Continuous Power Dissipation ($T_A = +70^{\circ}C$)
Narrow Plastic DIP (derate 14.29mW/°C above +70°C)1143mW
Wide SO (derate 12.50mW/°C above +70°C)1000mW
SSOP (derate 9.52mW/°C above +70°C)762mW
Narrow Ceramic SB (derate 20.00mW/°C above +70°C)1600mW

Operating Temperature Ranges	
MAX197_C	0°C to +70°C
MAX197_E	40°C to +85°C
MAX197_M	55°C to +125°C
Storage Temperature Range	
Lead Temperature (soldering, 10	0s)+300°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

 $(V_{DD} = 5V \pm 5\%; unipolar/bipolar range; external reference mode, V_{REF} = 4.096V; 4.7 \mu F at REF pin; external clock, f_{CLK} = 2.0 MHz with 50% duty cycle; T_A = T_{MIN} to T_{MAX}, unless otherwise noted.)$

PARAMETER	SYMBOL	COND	ITIONS	MIN	TYP	MAX	UNITS	
ACCURACY (Note 1)	•						•	
Resolution				12			Bits	
Integral Nonlinearity	INL	MAX197A				±1/2	LSB	
Integral Norllinearity	IINL	MAX197B				±1	— LSB	
Differential Nonlinearity	DNL					±1	LSB	
		Unipolar	MAX197A			±3		
Offset Error		Orlipolal	MAX197B			±5	LSB	
Oliset Elloi		Bipolar	MAX197A			±5	LOD	
		Біроіаі	MAX197B			±10	1	
Channel-to-Channel Offset		Unipolar			±0.1		LSB	
Error Matching		Bipolar			±0.5		LOD	
Gain Error		Unipolar	MAX197A			±7	- LSB	
		Опрова	MAX197B			±10		
(Note 2)		Bipolar	MAX197A			±7		
		Біроіаі	MAX197B			±10		
Gain Temperature Coefficient		Unipolar Bipolar			3		ppm/°C	
(Note 2)					5			
DYNAMIC SPECIFICATIONS (1	OkHz sine-w	ave input, ±10Vp-p, fsA	MPLE = 100ksps)					
Signal-to-Noise + Distortion Ratio	SINAD		MAX197A	70			- dB	
Signal-to-Noise + Distortion hatto	SINAD		MAX197B	69			ub	
Total Harmonic Distortion	THD	Up to the 5th harmonic			-85	-78	dB	
Spurious-Free Dynamic Range	SFDR			80			dB	
Channel-to-Channel Crosstalk		50kHz, V _{IN} = ±5V (Note 3)			-86		dB	
Aperture Delay		External CLK mode/external acquisition control			15		ns	
Aperture Jitter		External CLK mode/excontrol	ternal acquisition		<50		ps	
Aportare officer		Internal CLK mode/inte control (Note 4)	ernal acquisition		10		ns	

ELECTRICAL CHARACTERISTICS (continued)

 $(V_{DD} = 5V \pm 5\%; unipolar/bipolar range; external reference mode, V_{REF} = 4.096V; 4.7 \mu F at REF pin; external clock, f_{CLK} = 2.0 MHz with 50% duty cycle; T_A = T_{MIN} to T_{MAX}, unless otherwise noted.)$

PARAMETER	SYMBOL	CONE	DITIONS	MIN	TYP	MAX	UNITS
ANALOG INPUT		<u>I</u>					
Track/Hold Acquisition Time		f _{CLK} = 2.0MHz				3	μs
			±10V range		5		
0 110: 15 1:11		0.15 11 (±5V range		2.5		
Small-Signal Bandwidth		-3dB rolloff	0V to 10V range		2.5		- MHz
		0V to 5V range			1.25		
		Llaineles		0		10	
Input Voltage Range		Unipolar		0		5	V
(See Table 1)		Dinalar		-10		10	V
		Bipolar		-5		5	
		Unipolar	0V to 10V range			720	
Innest Course		Unipolar	0V to 5V range			360	
Input Current		Dinolor	-10V to 10V range	-1200		720	μΑ
		Bipolar	-5V to 5V range	-600		360	1
Input Dynamia Pasiatanas		Unipolar			21		kΩ
Input Dynamic Resistance		Bipolar			16		, NS2
Input Capacitance		(Note 5)				40	pF
INTERNAL REFERENCE							
REF Output Voltage	V _{REF}	T _A = +25°C		4.076	4.096	4.116	V
REF Output Tempco	TC VREF				40		ppm/°C
Output Short-Circuit Current						30	mA
Load Regulation		0mA to 0.5mA output of	current (Note 6)			7.5	mV
Capacitive Bypass at REF				4.7			μF
REFADJ Output Voltage				2.465	2.500	2.535	V
REFADJ Adjustment Range		With recommended ci	rcuit (Figure 1)		±1.5		%
Buffer Voltage Gain					1.6384		V/V
REFERENCE INPUT (Buffer d	sabled, refere	ence input applied to RE	EF pin)				
Input Voltage Range				2.4		4.18	V
Input Current		V _{REF} = 4.18V	Normal or STANDBY power-down mode			400	μΑ
input Current		VREF - 4.10V	FULL power-down mode			1	μΑ
Input Resistance		Normal or STANDBY p	oower-down mode	10			kΩ
input nesistance		FULL power-down mo	de	5			MΩ
REFADJ Threshold for Buffer Disable				V _{DD} - 50	mV		V



ELECTRICAL CHARACTERISTICS (continued)

 $(V_{DD} = 5V \pm 5\%$; unipolar/bipolar range; external reference mode, $V_{REF} = 4.096V$; $4.7\mu F$ at REF pin; external clock, $f_{CLK} = 2.0MHz$ with 50% duty cycle; $T_{A} = T_{MIN}$ to T_{MAX} , unless otherwise noted.)

PARAMETER	SYMBOL	COND	ITIONS	MIN	TYP	MAX	UNITS	
POWER REQUIREMENTS		I						
Supply Voltage	V_{DD}			4.75		5.25	V	
		Normal mode, bipolar ranges				18	^	
Cupaly Current	loo	Normal mode, unipolar	ranges		6	10	mA	
Supply Current	IDD	Standby power-down (STBYPD)		700	850		
		Full power-down mode	(FULLPD) (Note 7)			120	μΑ	
Power-Supply Rejection Ratio	PSRR	External reference = 4.	096V			±1/2	LSB	
(Note 8)	PORR	Internal reference			±1/2		LOD	
TIMING				·				
Internal Clock Frequency	fclk	C _{CLK} = 100pF		1.25	1.56	2.00	MHz	
External Clock Frequency Range	fclk			0.1		2.0	MHz	
	tacqi	Internal acquisition	External CLK	3.0				
Acquisition Time	IACQI	Internal CLK		3.0		5.0	μs	
Acquisition Time	tacor	External acquisition (Note 9)		3.0				
	tacqe	After FULLPD or STBYPD			5			
Conversion Time	tCONV	External CLK Internal CLK, C _{CLK} = 100pF		6.0			μs	
Conversion Time	ICONV			6.0	7.7	10.0		
Throughput Rate		External CLK				100	ksps	
moughput nate		Internal CLK, C _{CLK} = 1	00pF	62			, vaha	
Bandgap Reference Start-Up Time		Power-up (Note 10)			200		μs	
Deference Duffer Cettling		To 0.1mV REF bypass	C _{REF} = 4.7µF		8		1	
Reference Buffer Settling		capacitor fully discharged	C _{REF} = 33µF		60		- ms	
DIGITAL INPUTS (D7-D0, CLK,	RD, WR, CS	S, HBEN, SHDN) (Note 1	1)					
Input High Voltage	V _{INH}			2.4			V	
Input Low Voltage	VINL					0.8	V	
Input Leakage Current	liN	V _{IN} = 0V or V _{DD}			±10	μΑ		
Input Capacitance	CIN	(Note 5)				15	pF	
DIGITAL OUTPUTS (D7-D4, D3,	/D11, D2/D1	10, D1/D9, D0/D8, INT)						
Output Low Voltage	V _{OL}	$V_{DD} = 4.75V, I_{SINK} = 1$	V _{DD} = 4.75V, I _{SINK} = 1.6mA			0.4	V	
Output High Voltage	VoH	V _{DD} = 4.75V, I _{SOURCE}	= 1mA	V _{DD} - 1			V	
Three-State Output Capacitance	Cout	(Note 5)				15	pF	

TIMING CHARACTERISTICS

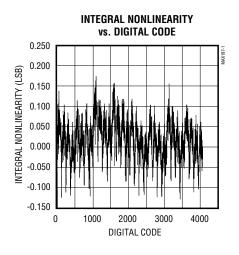
 $(V_{DD} = 5V \pm 5\%; unipolar/bipolar range; external reference mode, V_{REF} = 4.096V; 4.7\mu F at REF pin; external clock, f_{CLK} = 2.0MHz with 50% duty cycle; T_A = T_{MIN} to T_{MAX}, unless otherwise noted.)$

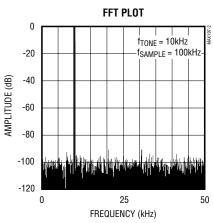
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
CS Pulse Width	tcs		80			ns
WR Pulse Width	twR		80			ns
CS to WR Setup Time	tcsws		0			ns
CS to WR Hold Time	tcswh		0			ns
CS to RD Setup Time	tcsrs		0			ns
CS to RD Hold Time	tcsrh		0			ns
CLK to WR Setup Time	tcws				100	ns
CLK to WR Hold Time	tcwH				50	ns
Data Valid to WR Setup	tDS		60			ns
Data Valid to WR Hold	tDH		0			ns
RD Low to Output Data Valid	t _{DO}	Figure 2, C _L = 100pF (Note 12)			120	ns
HBEN High or HBEN Low to Output Valid	tDO1	Figure 2, C _L = 100pF (Note 12)			120	ns
RD High to Output Disable	trr	(Note 13)			70	ns
RD Low to INT High Delay	tint1				120	ns

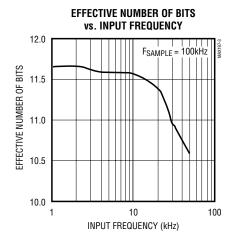
- **Note 1:** Accuracy specifications tested at V_{DD} = 5.0V. Performance at power-supply tolerance limits guaranteed by Power-Supply Rejection test. Tested for the ±10V input range.
- Note 2: External reference: VREF = 4.096V, offset error nulled, ideal last code transition = FS 3/2LSB.
- **Note 3:** Ground "on" channel; sine wave applied to all "off" channels.
- **Note 4:** Maximum full-power input frequency for 1LSB error with 10ns jitter = 3kHz.
- Note 5: Guaranteed by design. Not tested.
- Note 6: Use static loads only.
- Note 7: Tested using internal reference.
- Note 8: PSRR measured at full-scale.
- Note 9: External acquisition timing: starts at data valid at ACQMOD = low control byte; ends at rising edge of WR with ACQMOD = high control byte.
- **Note 10:** Not subject to production testing. Provided for design guidance only.
- **Note 11:** All input control signals specified with $t_R = t_F = 5$ ns from a voltage level of 0.8V to 2.4V.
- Note 12: t_{DO} and t_{DO1} are measured with the load circuits of Figure 2 and defined as the time required for an output to cross 0.8V or 2.4V.
- Note 13: ttp is defined as the time required for the data lines to change by 0.5V.

Typical Operating Characteristics

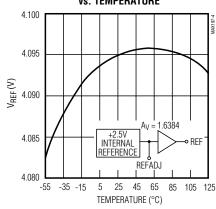
 $(T_A = +25$ °C, unless otherwise noted.)



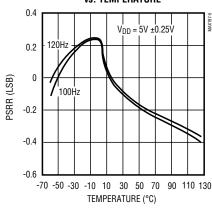




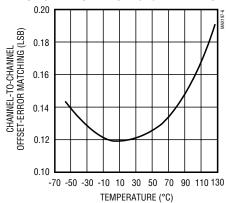
REFERENCE OUTPUT VOLTAGE (V_{REF}) vs. Temperature



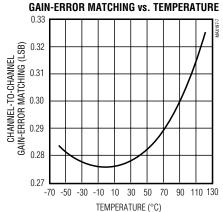




CHANNEL-TO-CHANNEL
OFFSET-ERROR MATCHING vs. TEMPERATURE



CHANNEL-TO-CHANNEL
GAIN-FRROR MATCHING VS. TEMPERATURE



Pin Description

PIN	NAME	FUNCTION
1	CLK	Clock Input. In external clock mode, drive CLK with a TTL/CMOS compatible clock. In internal clock mode, place a capacitor from this pin to ground to set the internal clock frequency; $f_{CLK} = 1.56MHz$ typical with $C_{CLK} = 100pF$.
2	CS	Chip Select, active low.
3	WR	When $\overline{\text{CS}}$ is low, in the internal acquisition mode, a rising edge on $\overline{\text{WR}}$ latches in configuration data and starts an acquisition plus a conversion cycle. When $\overline{\text{CS}}$ is low, in the external acquisition mode, the first rising edge on $\overline{\text{WR}}$ starts an acquisition and a second rising edge on $\overline{\text{WR}}$ ends acquisition and starts a conversion cycle.
4	RD	If $\overline{\text{CS}}$ is low, a falling edge on $\overline{\text{RD}}$ will enable a read operation on the data bus.
5	HBEN	Used to multiplex the 12-bit conversion result. When high, the 4 MSBs are multiplexed on the data bus; when low, the 8 LSBs are available on the bus.
6	SHDN	Shutdown. Puts the device into full power-down (FULLPD) mode when pulled low.
7–10	D7-D4	Three-State Digital I/O
11	D3/D11	Three-State Digital I/O. D3 output (HBEN = low), D11 output (HBEN = high).
12	D2/D10	Three-State Digital I/O. D2 output (HBEN = low), D10 output (HBEN = high).
13	D1/D9	Three-State Digital I/O. D1 output (HBEN = low), D9 output (HBEN = high).
14	D0/D8	Three-State Digital I/O. D0 output (HBEN = low), D8 output (HBEN = high). D0 = LSB.
15	AGND	Analog Ground
16–23	CH0-CH7	Analog Input Channels
24	INT	INT goes low when conversion is complete and output data is ready.
25	REFADJ	Bandgap Voltage-Reference Output/External Adjust Pin. Bypass with a $0.01\mu F$ capacitor to AGND. Connect to V_{DD} when using an external reference at the REF pin.
26	REF	Reference Buffer Output/ADC Reference Input. In internal reference mode, the reference buffer provides a 4.096V nominal output, externally adjustable at REFADJ. In external reference mode, disable the internal buffer by pulling REFADJ to VDD.
27	V _{DD}	+5V Supply. Bypass with 0.1μF capacitor to AGND.
28	DGND	Digital Ground

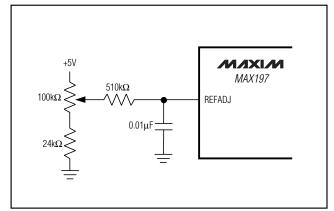


Figure 1. Reference-Adjust Circuit

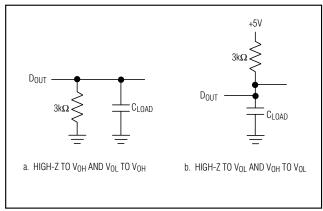


Figure 2. Load Circuits for Enable Time

Detailed Description

Converter Operation

The MAX197, a multi-range, fault-tolerant ADC, uses successive approximation and internal input track/hold (T/H) circuitry to convert an analog signal to a 12-bit digital output. The parallel-output format provides easy interface to microprocessors (μ Ps). Figure 3 shows the MAX197 in its simplest operational configuration.

Analog-Input Track/Hold

In the internal acquisition control mode (control bit D5 set to 0), the T/H enters its tracking mode on \overline{WR} 's rising edge, and enters its hold mode when the internally timed (6 clock cycles) acquisition interval ends. A low impedance input source, which settles in less than 1.5 μ s, is required to maintain conversion accuracy at the maximum conversion rate.

In the external acquisition control mode (D5 = 1), the T/H enters its tracking mode on the first \overline{WR} rising edge and enters its hold mode when it detects the second \overline{WR} rising edge with D5 = 0. See the *External Acquisition* section.

Input Bandwidth

The ADC's input tracking circuitry has a 5MHz small-signal bandwidth. When using the internal acquisition

mode with an external clock frequency of 2MHz, a 100ksps throughput rate can be achieved. It is possible to digitize high-speed transient events and measure periodic signals with bandwidths exceeding the ADC's sampling rate by using undersampling techniques. To avoid high-frequency signals being aliased into the frequency band of interest, anti-alias filtering is recommended (MAX274/MAX275 continuous-time filters).

Input Range and Protection

Figure 4 shows the equivalent input circuit. With VREF = 4.096V, the MAX197 can be programmed for input ranges of $\pm 10V$, $\pm 5V$, 0V to 10V, or 0V to 5V by setting the appropriate control bits (D3, D4) in the control byte (see Tables 2 and 3). The full-scale input voltage depends on the voltage at REF (Table 1). When an external reference is applied at REFADJ, the voltage at REF is given by VREF = $1.6384 \times VREFADJ$ (2.4V < VREF < 4.18V).

Table 1. Full Scale and Zero Scale

RANGE (V)	ZERO SCALE (V)	-FULL SCALE	+FULL SCALE
0 to 5	0	_	V _{REF} x 1.2207
0 to 10	0	_	V _{REF} x 2.4414
±5	_	-V _{REF} x 1.2207	V _{REF} x 1.2207
±10	_	-VREF x 2.4414	VREF x 2.4414

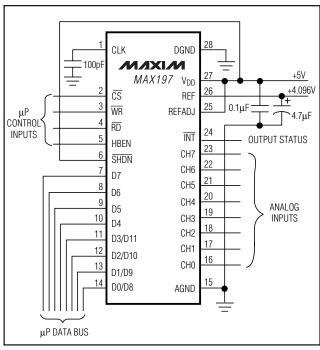


Figure 3. Operational Diagram

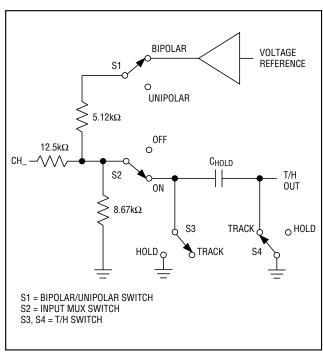


Figure 4. Equivalent Input Circuit

The input channels are overvoltage protected to ± 16.5 V. This protection is active even if the device is in power-down mode.

Even with $V_{DD} = 0V$, the input resistive network provides current-limiting that adequately protects the device.

Digital Interface

Input data (control byte) and output data are multiplexed on a three-state parallel interface. This parallel I/O can easily be interfaced with a $\mu P.$ $\overline{CS},$ $\overline{WR},$ and \overline{RD} control the write and read operations. \overline{CS} is the standard chipselect signal, which enables a μP to address the MAX197 as an I/O port. When high, it disables the \overline{WR} and \overline{RD} inputs and forces the interface into a high-Z state.

Input Format

The control byte is latched into the device, on pins D7–D0, during a write cycle. Table 2 shows the control-byte format.

Output Data Format

The output data format is binary in unipolar mode and twos-complement binary in bipolar mode. When reading the output data, \overline{CS} , and \overline{RD} must be low. When HBEN is low, the lower eight bits are read. When HBEN is high, the upper four MSBs are available and the output data bits D4–D7 are either set low (in unipolar mode) or set to the value of the MSB (in bipolar mode) (Table 6).

Table 2. Control-Byte Format

D7 (MSB)	D6	D5	D4	D3	D2	D1	D0 (LSB)
PD1	PD0	ACQMOD	RNG	BIP	A2	A1	A0

BIT	NAME	DESCRIPTION		
7, 6	7, 6 PD1, PD0 These two bits select the clock and power-down modes (Table 4).			
5	ACQMOD	0 = internally controlled acquisition (6 clock cycles), 1 = externally controlled acquisition		
4	RNG Selects the full-scale voltage magnitude at the input (Table 3).			
3 BIP Selects unipolar or bipolar conversion mode (Table 3).				
2, 1, 0	A2, A1, A0	These are address bits for the input mux to select the "on" channel (Table 5).		

Table 3. Range and Polarity Selection

BIP	RNG	INPUT RANGE (V)
0	0	0 to 5
0	1	0 to 10
1	0	±5
1	1	±10

Table 4. Clock and Power-Down Selection

PD1	PD1 PD0 DEVICE MODE	
0	0	Normal Operation / External Clock Mode
0	1	Normal Operation / Internal Clock Mode
1	0	Standby Power-Down (STBYPD); clock mode is unaffected
1	1	Full Power-Down (FULLPD); clock mode is unaffected

Table 5. Channel Selection

A2	A 1	A0	CH0	CH1	CH2	СНЗ	CH4	CH5	CH6	CH7
0	0	0	_							
0	0	1								
0	1	0			_					
0	1	1								
1	0	0					_			
1	0	1								
1	1	0								
1	1	1								

Table 6. Data-Bus Output

PIN	HBEN = LOW	HBEN = HIGH		
D0	B0 (LSB)	B8		
D1	B1	B9		
D2	B2	B10		
D3	B3	B11 (MSB)		
D4	B4	B11 (BIP = 1) / 0 (BIP = 0)		
D5	B5	B11 (BIP = 1) / 0 (BIP = 0)		
D6	B6	B11 (BIP = 1) / 0 (BIP = 0)		
D7	B7	B11 (BIP = 1) / 0 (BIP = 0)		

How to Start a Conversion

Conversions are initiated with a write operation, which selects the mux channel and configures the MAX197 for either unipolar or bipolar input range. A write pulse (WR + CS) can either start an acquisition interval or initiate a combined acquisition plus conversion. The sampling interval occurs at the end of the acquisition interval. The ACQMOD bit in the input control byte offers two options for acquiring the signal: internal or external. The conversion period lasts for 12 clock cycles in either internal or external clock or acquisition mode.

Writing a new control byte during conversion cycle will abort conversion and start a new acquisition interval.

Internal Acquisition

Select internal acquisition by writing the control byte with the ACQMOD bit cleared (ACQMOD = 0). This causes the write pulse to initiate an acquisition interval whose duration is internally timed. Conversion starts when this six-clock-cycle acquisition interval (3 μ s with fCLK = 2MHz) ends. See Figure 5.

External Acquisition

Use the external acquisition timing mode for precise control of the sampling aperture and/or independent control of acquisition and conversion times. The user controls acquisition and start-of-conversion with two separate write pulses. The first pulse, written with ACQMOD = 1, starts an acquisition interval of indeterminate length. The second write pulse, written with ACQMOD = 0, terminates acquisition and starts conversion on \overline{WR} 's rising edge (Figure 6). However, if the second control byte contains ACQMOD = 1, an indefinite acquisition interval is restarted.

The address bits for the input mux must have the same values on the first and second write pulses. Powerdown mode bits (PD0, PD1) can assume new values on the second write pulse (see *Power-Down Mode*).

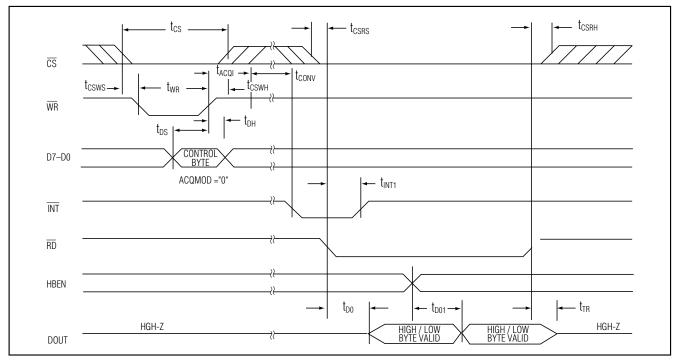


Figure 5. Conversion Timing Using Internal Acquisition Mode

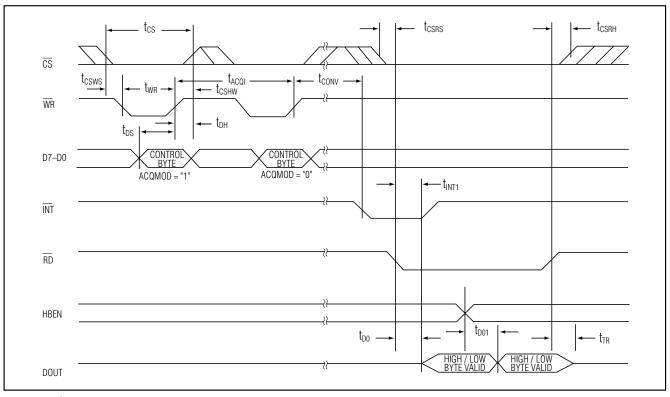


Figure 6. Conversion Timing Using External Acquisition Mode

How to Read a Conversion

A standard interrupt signal, INT, is provided to allow the device to flag the μP when the conversion has ended and a valid result is available. $\overline{\text{INT}}$ goes low when conversion is complete and the output data is ready (Figures 5 and 6). It returns high on the first read cycle or if a new control byte is written.

Clock Modes

The MAX197 operates with either an internal or an external clock. Control bits (D6, D7) select either internal or external clock mode. Once the desired clock mode is selected, changing these bits to program power-down will not affect the clock mode. In each mode, internal or external acquisition can be used. At power-up, external clock mode is selected.

Internal Clock Mode

Select internal clock mode to free the μP from the burden of running the SAR conversion clock. To select this mode, write the control byte with D7 = 0 and D6 = 1. A 100pF capacitor between the CLK pin and ground sets this frequency to 1.56MHz nominal. Figure 7

shows a linear relationship between the internal clock period and the value of the external capacitor used.

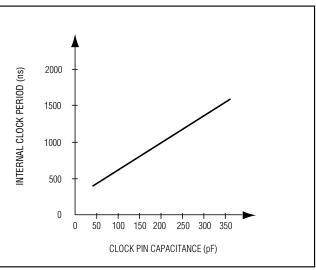


Figure 7. Internal Clock Period vs. Clock Pin Capacitance

External Clock Mode

Select external clock mode by writing the control byte with D7 = 0 and D6 = 0. Figure 8 shows CLK and \overline{WR} timing relationships in internal and external acquisition modes, with an external clock. A 100kHz to 2.0MHz

external clock with 45% to 55% duty cycle is required for proper operation. Operating at clock frequencies lower than 100kHz will cause a voltage droop across the hold capacitor, and subsequently degrade performance.

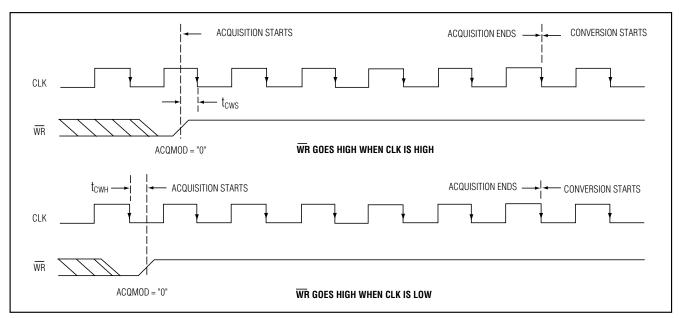


Figure 8a. External Clock and WR Timing (Internal Acquisition Mode)

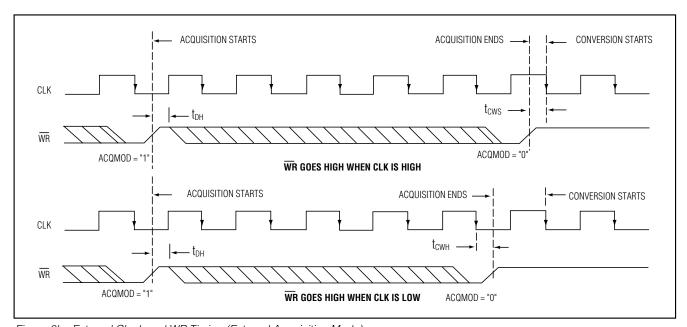


Figure 8b. External Clock and WR Timing (External Acquisition Mode)

Applications Information

Power-On Reset

At power-up, the internal power-supply circuitry sets $\overline{\text{INT}}$ high and puts the device in normal operation/external clock mode. This state is selected to keep the internal clock from loading the external clock driver when the part is used in external clock mode.

Internal or External Reference

The MAX197 can operate with either an internal or an external reference. An external reference can be connected to either the REF pin or to the REFADJ pin (Figure 9).

To use the REF input directly, disable the internal buffer by tying REFADJ to V_{DD} . Using the REFADJ input eliminates the need to buffer the reference externally. When the reference is applied at REFADJ, bypass REFADJ with a $0.01\mu F$ capacitor to AGND.

The REFADJ internal buffer gain is trimmed to 1.6384 to provide 4.096V at the REF pin from a 2.5V reference.

Internal Reference

The internally trimmed 2.50V reference is gained through the REFADJ buffer to provide 4.096V at REF. Bypass the REF pin with a 4.7 μ F capacitor to AGND and the REFADJ pin with a 0.01 μ F capacitor to AGND. The internal reference voltage is adjustable to $\pm 1.5\%$ (± 65 LSBs) with the reference-adjust circuit of Figure 1.

External Reference

At REF and REFADJ, the input impedance is a minimum of $10k\Omega$ for DC currents. During conversions, an

external reference at REF must be able to deliver 400 μ A DC load currents, and must have an output impedance of 10 Ω or less. If the reference has higher input impedance or is noisy, bypass it close to the REF pin with a 4.7 μ F capacitor to AGND.

With an external reference voltage of less than 4.096V at the REF pin or less than 2.5V at the REFADJ pin, the increase in the ratio of the RMS noise to the LSB value (FS / 4096) results in performance degradation (loss of effective bits).

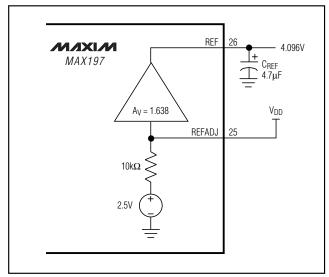


Figure 9b. External Reference, Reference at REF

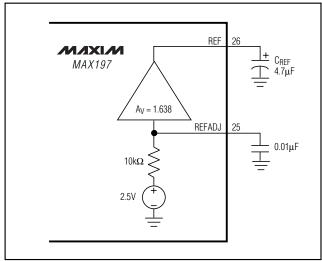


Figure 9a. Internal Reference

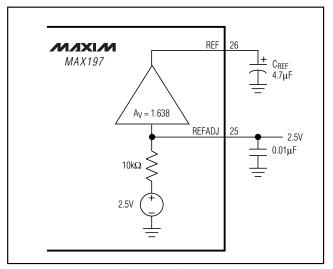


Figure 9c. External Reference, Reference at REFADJ

Power-Down Mode

To save power, you can put the converter into low-current shutdown mode between conversions. Two programmable power-down modes are available, in addition to a hardware shutdown. Select STBYPD or FULLPD by programming PD0 and PD1 in the input control byte. When software power-down is asserted, it becomes effective only after the end of conversion. In all power-down modes, the interface remains active and conversion results may be read. Input overvoltage protection is active in all power-down modes. The device returns to normal operation on the first WR falling edge during write operation.

For hardware-controlled (FULLPD) power-down, pull the SHDN pin low. When hardware shutdown is asserted, it becomes effective immediately and the conversion is aborted.

Choosing Power-Down Modes

The bandgap reference and reference buffer remain active in STBYPD mode, maintaining the voltage on the $4.7\mu F$ capacitor at the REF pin. This is a "DC" state that does not degrade after power-down of any duration. Therefore, you can use any sampling rate with this mode, without regard to start-up delays.

However, in FULLPD mode, only the bandgap reference is active. Connect a 33µF capacitor between REF and AGND to maintain the reference voltage between conversion and to reduce transients when the buffer is enabled and disabled. Throughput rates down to 1ksps can be achieved without allotting extra acquisition time for reference recovery prior to conversion. This allows conversion to begin immediately after power-down ends. If the discharge of the REF capacitor during FULLPD exceeds the desired limits for accuracy (less than a fraction of an LSB), run a STBYPD power-down cycle prior to starting conversions. Take into account that the reference buffer recharges the bypass capacitor at an 80mV/ms slew rate and add 50µs for settling time. Throughput rates of 10ksps offer typical supply currents of 470µA, using the recommended 33µF capacitor value.

Auto-Shutdown

Selecting STBYPD on every conversion automatically shuts the MAX197 down after each conversion without requiring any start-up time on the next conversion.

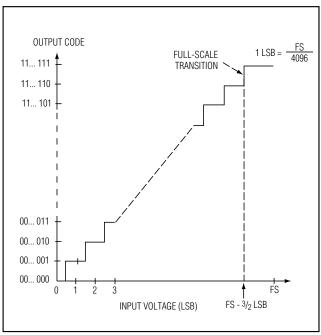


Figure 10. Unipolar Transfer Function

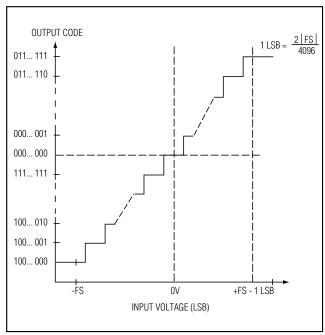


Figure 11. Bipolar Transfer Function

Transfer Function

Output data coding for the MAX197 is binary in unipolar mode with 1LSB = (FS / 4096) and two's-complement binary in bipolar mode with 1LSB = ((2 x |FS|) / 4096). Code transitions occur halfway between successive-integer LSB values. Figures 10 and 11 show the input/output (I/O) transfer functions for unipolar and bipolar operations, respectively. For full-scale (FS) values, see Table 1.

Layout, Grounding, and Bypassing

Careful printed circuit board layout is essential for best system performance. For best performance, use a ground plane. To reduce crosstalk and noise injection, keep analog and digital signals separate. Digital ground lines can run between digital signal lines to minimize interference. Connect analog grounds and DGND in a star configuration to AGND. For noise-free operation, ensure the ground return from AGND to the supply ground is low impedance and as short as possible. Connect the logic grounds directly to the supply ground. Bypass V_{DD} with $0.1\mu F$ and $4.7\mu F$ capacitors to AGND to minimize high- and low-frequency fluctuations. If the supply is excessively noisy, connect a 5Ω resistor between the supply and V_{DD} , as shown in Figure 12.

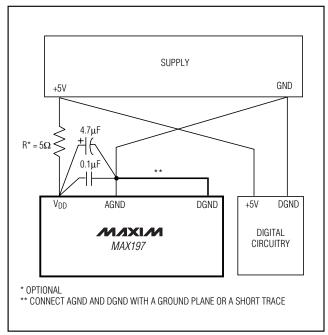


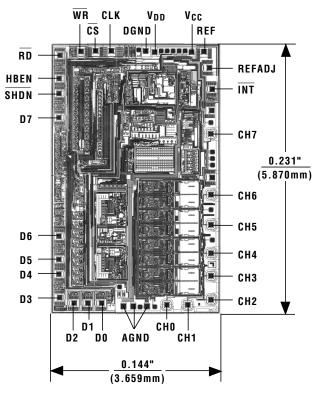
Figure 12. Power-Supply Grounding Connection

_Ordering Information (continued)

PART	TEMP RANGE	PIN-PACKAGE
MAX197AENI	-40°C to +85°C	28 Narrow Plastic DIP
MAX197BENI	-40°C to +85°C	28 Narrow Plastic DIP
MAX197AEWI	-40°C to +85°C	28 Wide SO
MAX197BEWI	-40°C to +85°C	28 Wide SO
MAX197AEAI	-40°C to +85°C	28 SSOP
MAX197BEAI	-40°C to +85°C	28 SSOP
MAX197AMYI	-55°C to +125°C	28 Narrow Ceramic SB**
MAX197BMYI	-55°C to +125°C	28 Narrow Ceramic SB**

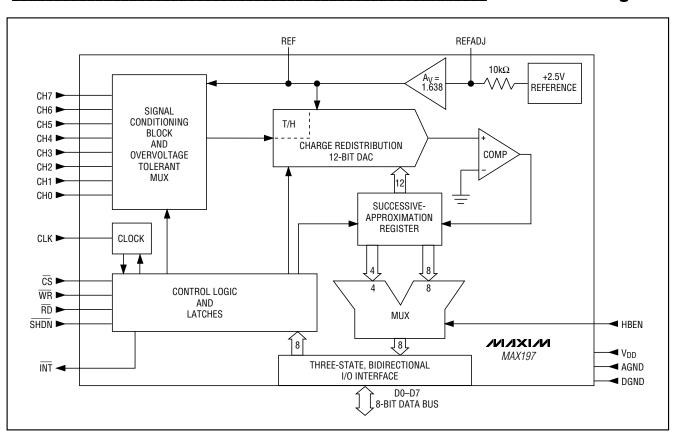
^{**} Contact factory for availability and processing to MIL-STD-883.

Chip Topography



TRANSISTOR COUNT: 2956 SUBSTRATE CONNECTED TO GND

Functional Diagram



Maxim cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a Maxim product. No circuit patent licenses are implied. Maxim reserves the right to change the circuitry and specifications without notice at any time.

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Maxim Integrated:

MAX197BCNI+ MAX197BENI+ MAX197BMWI/PR